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# 2SJ172

Silicon P-Channel MOS FET

# HITACHI

November 1996

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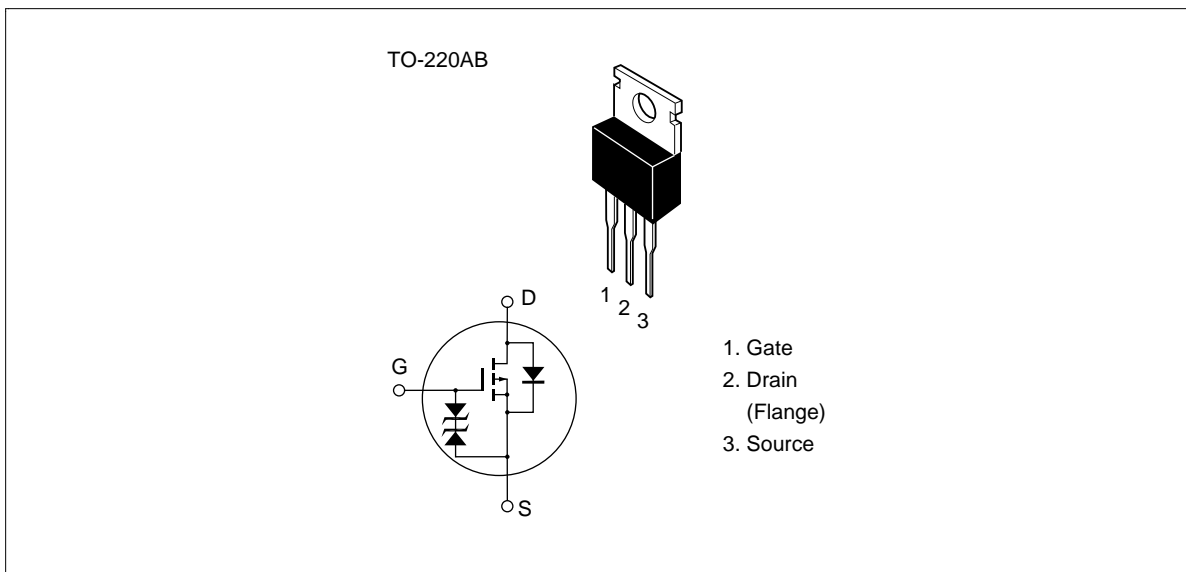
## Application

High speed power switching

## Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device
  - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

## Outline



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### Absolute Maximum Ratings (Ta = 25°C)

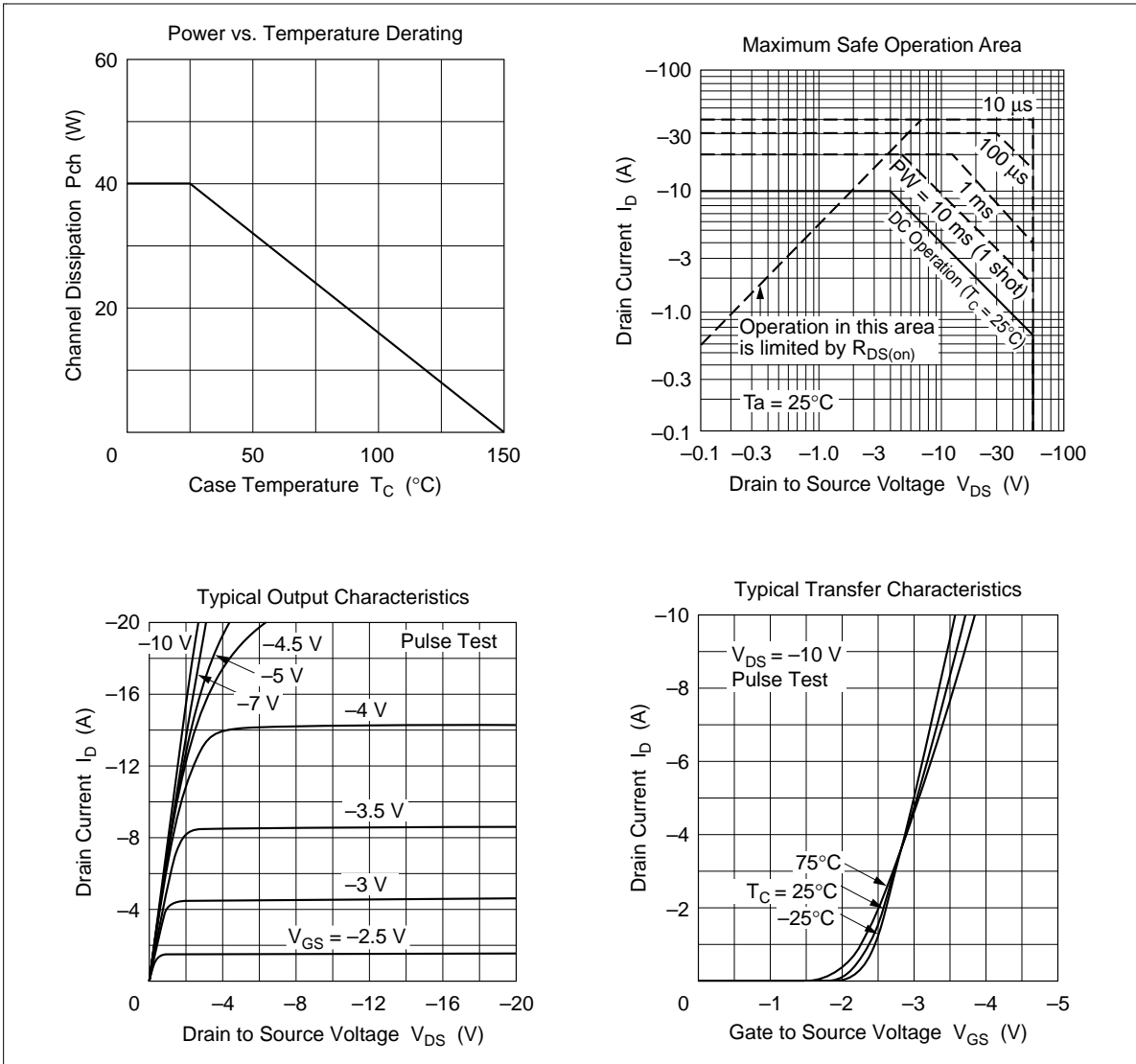
Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	-60	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	$I_D$	-10	A
Drain peak current	$I_{D(pulse)}^{*1}$	-40	A
Body to drain diode reverse drain current	$I_{DR}$	-10	A
Channel dissipation	Pch*2	40	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

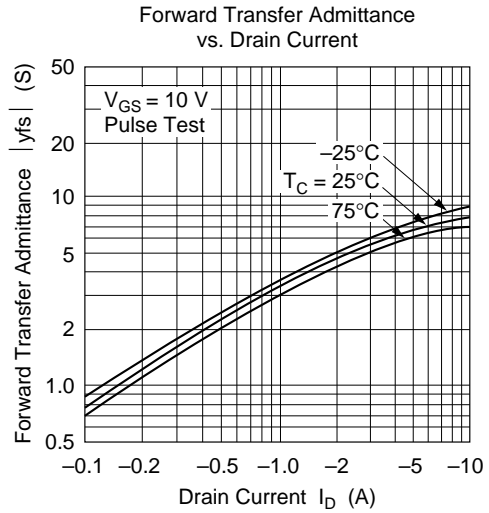
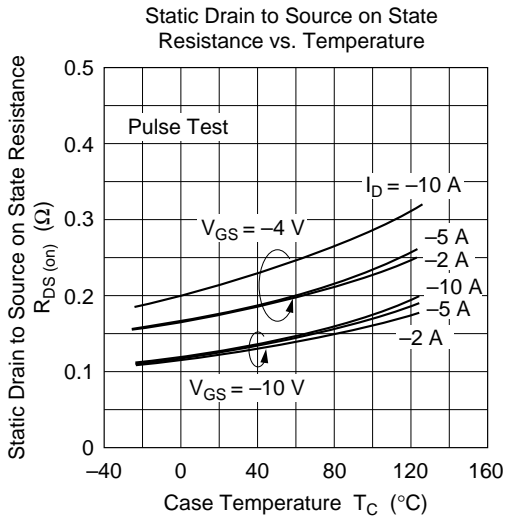
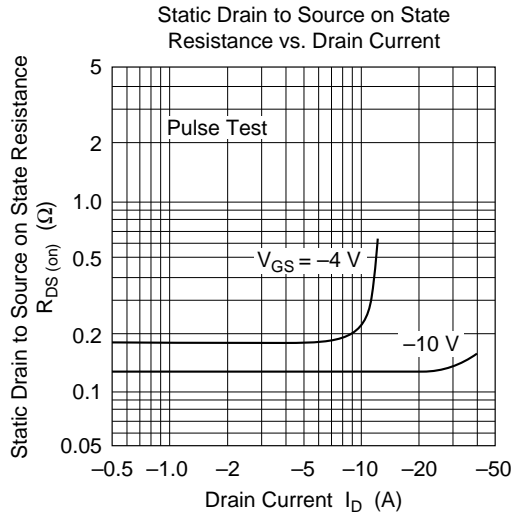
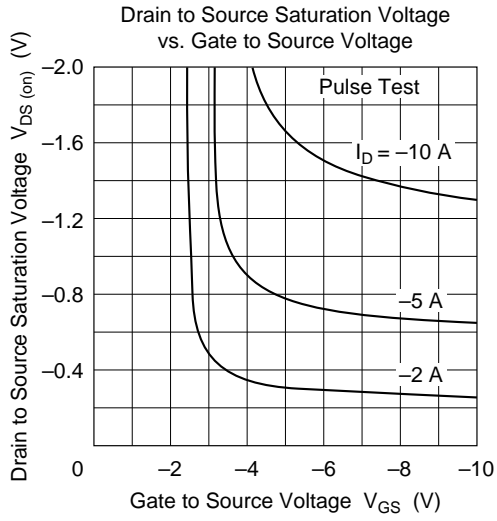
Notes 1.  $PW \leq 10 \mu s$ , duty cycle  $\leq 1\%$   
 2. Value at  $T_c = 25^\circ C$

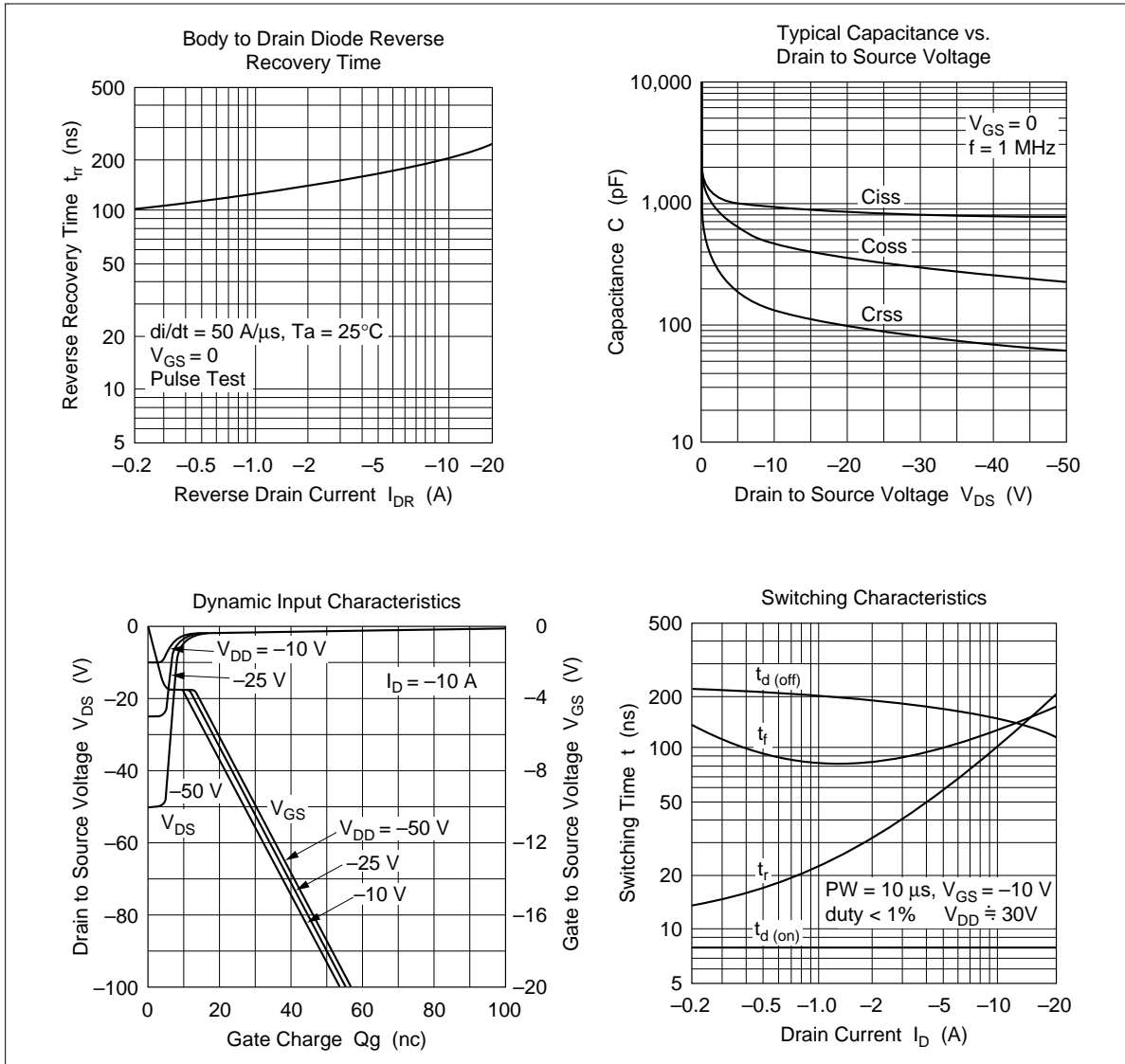
### Electrical Characteristics (Ta = 25°C)

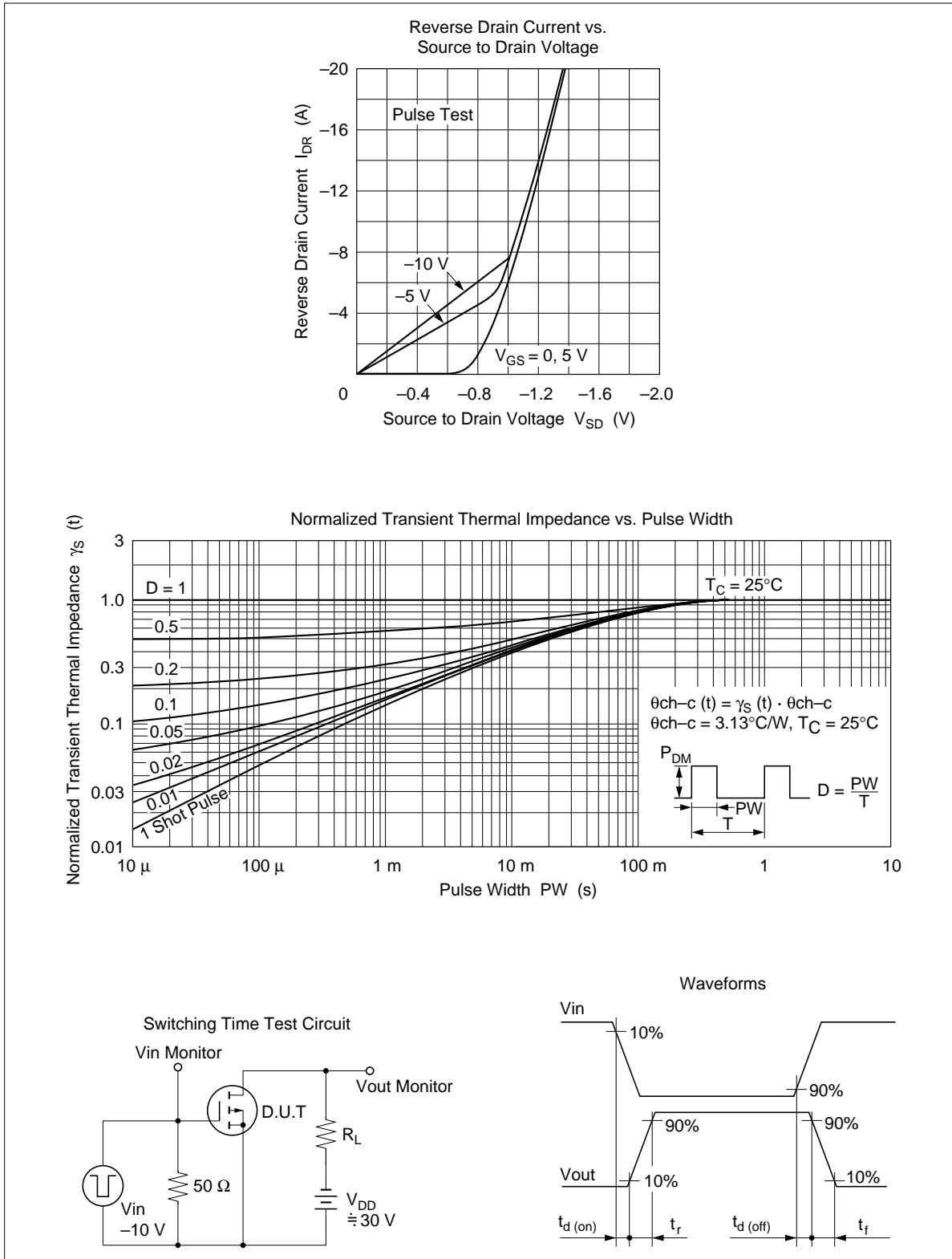
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-60	—	—	V	$I_D = -10 \text{ mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100 \mu A$ , $V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	±10	μA	$V_{GS} = \pm 16 \text{ V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	250	μA	$V_{DS} = -50 \text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$I_D = -1 \text{ mA}$ , $V_{DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.13	0.18	Ω	$I_D = -5 \text{ A}$ , $V_{GS} = -10 \text{ V}^{*1}$
		—	0.18	0.25		$I_D = -5 \text{ A}$ , $V_{GS} = -4 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	4.0	6.5	—	S	$I_D = -5 \text{ A}$ , $V_{DS} = -10 \text{ V}^{*1}$
Input capacitance	Ciss	—	900	—	pF	$V_{DS} = -10 \text{ V}$ , $V_{GS} = 0$ ,
Output capacitance	Coss	—	460	—	pF	f = 1 MHz
Reverse transfer capacitance	Crss	—	130	—	pF	
Turn-on delay time	$t_{d(on)}$	—	8	—	ns	$I_D = -5 \text{ A}$ , $V_{GS} = -10 \text{ V}$ ,
Rise time	$t_r$	—	65	—	ns	$R_L = 6 \Omega$
Turn-off delay time	$t_{d(off)}$	—	170	—	ns	
Fall time	$t_f$	—	105	—	ns	
Body to drain diode forward voltage	$V_{DF}$	—	-1.1	—	V	$I_F = -10 \text{ A}$ , $V_{GS} = 0$
Body to drain diode reverse recovery time	$t_{rr}$	—	200	—	ns	$I_F = -10 \text{ A}$ , $V_{GS} = 0$ , $di_F/dt = 50 \text{ A}/\mu s$

Note 1. Pulse test









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